

NPN LOW NOISE SILICON MICROWAVE TRANSISTOR

PRODUCT DATA SHEET

FEATURES:

- High Gain Bandwidth Product
 $f_t = 10 \text{ GHz typ @ } I_C = 40\text{mA}$
- Low Noise Figure
 1.4 dB typ at 1.0 GHz
 1.7 dB typ at 2.0 GHz
- High Gain
 $|S_{21}|^2 = 16.9 \text{ dB @ } 1.0 \text{ GHz}$
 $12.0 \text{ dB @ } 2.0 \text{ GHz}$
- Dice, Plastic, Hermetic and Surface Mount packages available

PERFORMANCE DATA:

- Electrical Characteristics ($T_A = 25^\circ\text{C}$)

DESCRIPTION AND APPLICATIONS:

Bipolarics' BRF640 is a high performance silicon bipolar transistor intended for use in low noise applications at VHF, UHF and microwave frequencies. These applications include narrowband and wideband amplifiers, oscillators and micropower transmitters. Typical applications include cellular telephone preamplifiers/mixers, CATV amplifiers and Part 15 receivers and transmitters. Commercial plastic, surface mount and hermetic (including Stripline) packaging options make this device very versatile; from consumer product to space flight.

Absolute Maximum Ratings:

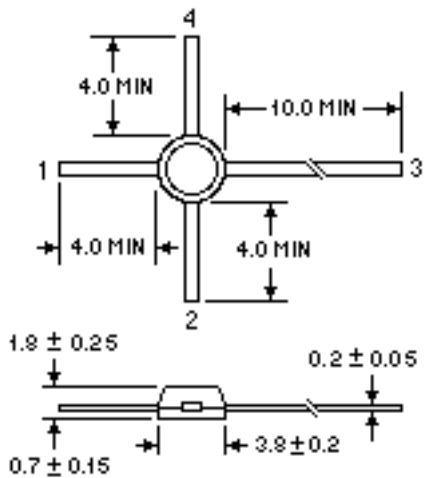
| SYMBOL | PARAMETERS | RATING | UNITS |
|-----------|---------------------------|------------|------------------|
| V_{CBO} | Collector-Base Voltage | 7 | V |
| V_{CEO} | Collector-Emitter Voltage | 7 | V |
| V_{EBO} | Emitter-Base Voltage | 1.5 | V |
| I_C | Collector Current | 80 | mA |
| T_J (1) | Junction Temperature | 200 | $^\circ\text{C}$ |
| T_{STG} | Storage Temperature | -65 to 150 | $^\circ\text{C}$ |

(1) Depends on package

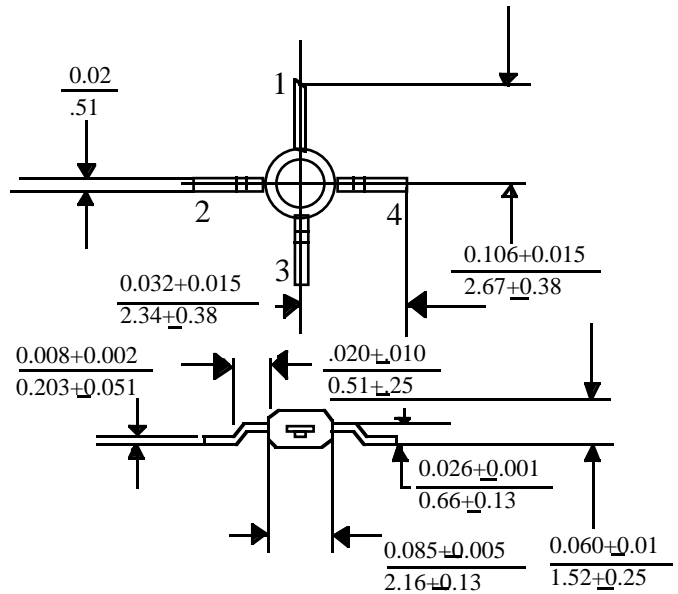
| SYMBOL | PARAMETERS & CONDITIONS $V_{CE} = 8\text{V}, I_C = 25 \text{ mA}$ unless stated | UNIT | MIN. | TYP. | MAX. |
|--------------|--|---------------|------|------|------|
| f_t | Gain Bandwidth Product | GHz | | 12.0 | |
| $ S_{21} ^2$ | Insertion Power Gain: | | | | |
| | $f = 1.0 \text{ GHz}$ | dB | | 16.9 | |
| | $f = 2.0 \text{ GHz}$ | dB | | 12.0 | |
| P_{1dB} | Power output at 1dB compression: | | | | |
| | $f = 1.0 \text{ GHz}$ | dBm | | 19.0 | |
| G_{1dB} | Gain at 1dB compression: | | | | |
| | $f = 1.0 \text{ GHz}$ | dBm | | 15.0 | |
| NF | Noise Figure: $V_{CE} = 8\text{V}, I_C = 10\text{mA}$ | | | | |
| | $f = 1.0 \text{ GHz}$ | dB | | 1.4 | |
| h_{FE} | Forward Current Transfer Ratio: $V_{CE} = 8\text{V}, I_C = 10 \text{ mA}$ | | | | |
| | $f = 1\text{MHz}$ | | 30 | 150 | 300 |
| I_{CBO} | Collector Cutoff Current : $V_{CB} = 8\text{V}$ | μA | | | 0.2 |
| I_{EBO} | Emitter Cutoff Current : $V_{EB} = 1\text{V}$ | μA | | | 1.0 |
| C_{CB} | Collector Base Capacitance: $V_{CB} = 8\text{V}$ | | | | |
| | $f = 1\text{MHz}$ | pF | | 0.30 | |

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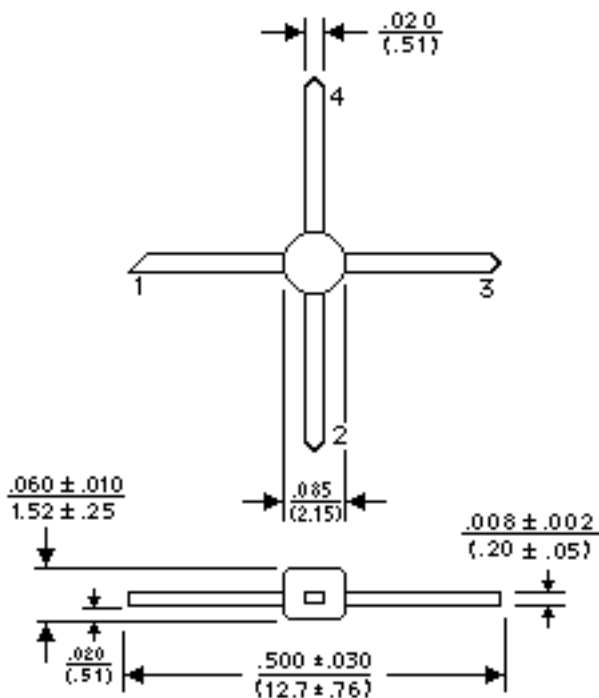
BRF64004
Package Style 04: 0.145" Plastic Macro-X



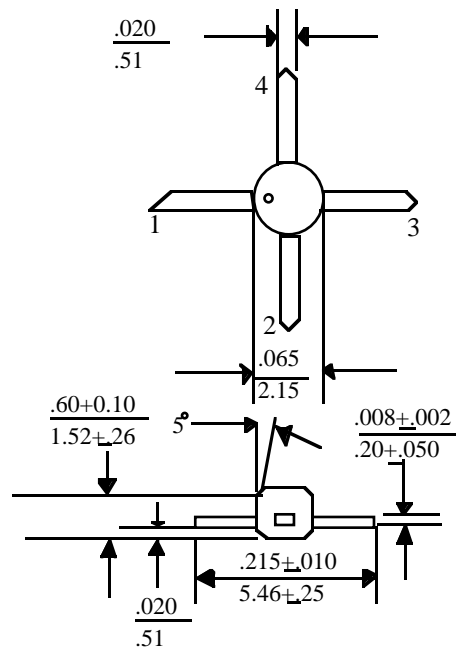
BRF64086
Package Style 86: 0.085" Plastic Micro-X,
Surface Mount



BRF6485
Package Style 85: 0.085" Plastic Micro-X



BRF64084
Package Style 84: 0.085" Plastic Micro-X,
Short Lead



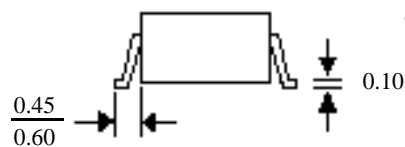
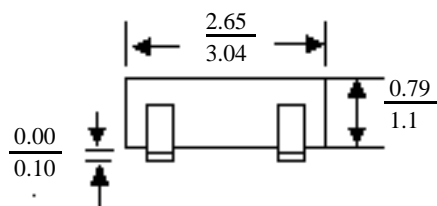
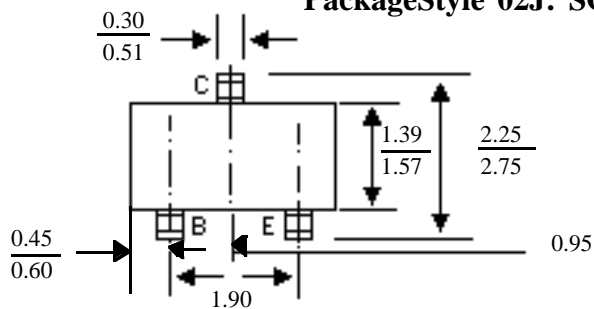
BIPOLARICS, INC.

Part Number BRF640

NPN LOW NOISE SILICON MICROWAVE TRANSISTOR

BRF64002J

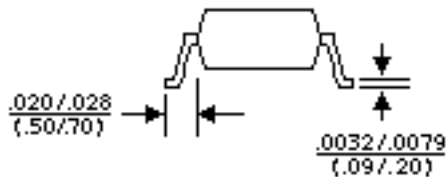
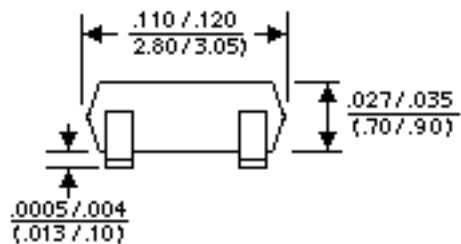
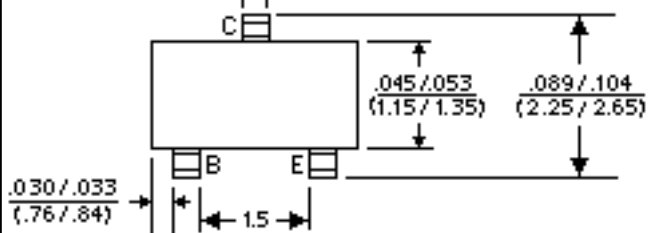
Package Style 02J: SOT-23J



$\frac{.015}{.018}$
(.37/.45)

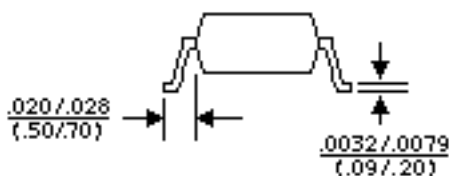
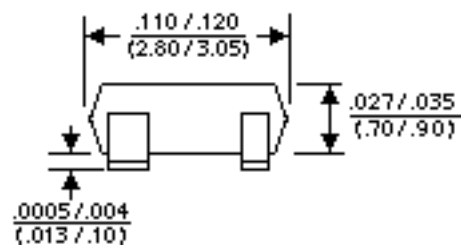
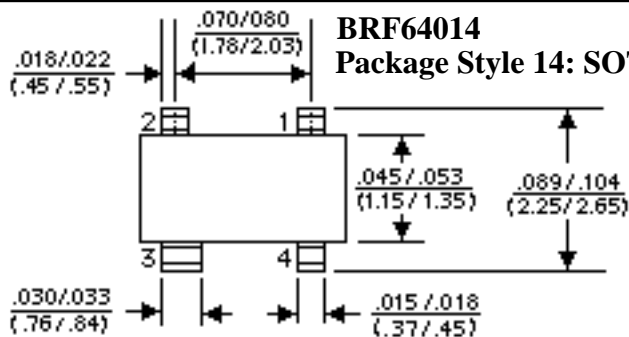
BRF64002

Package Style 02: SOT-23



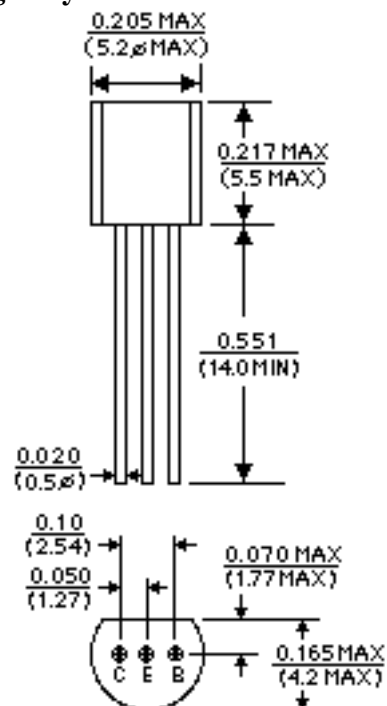
BRF64014

Package Style 14: SOT-143



BRF64092

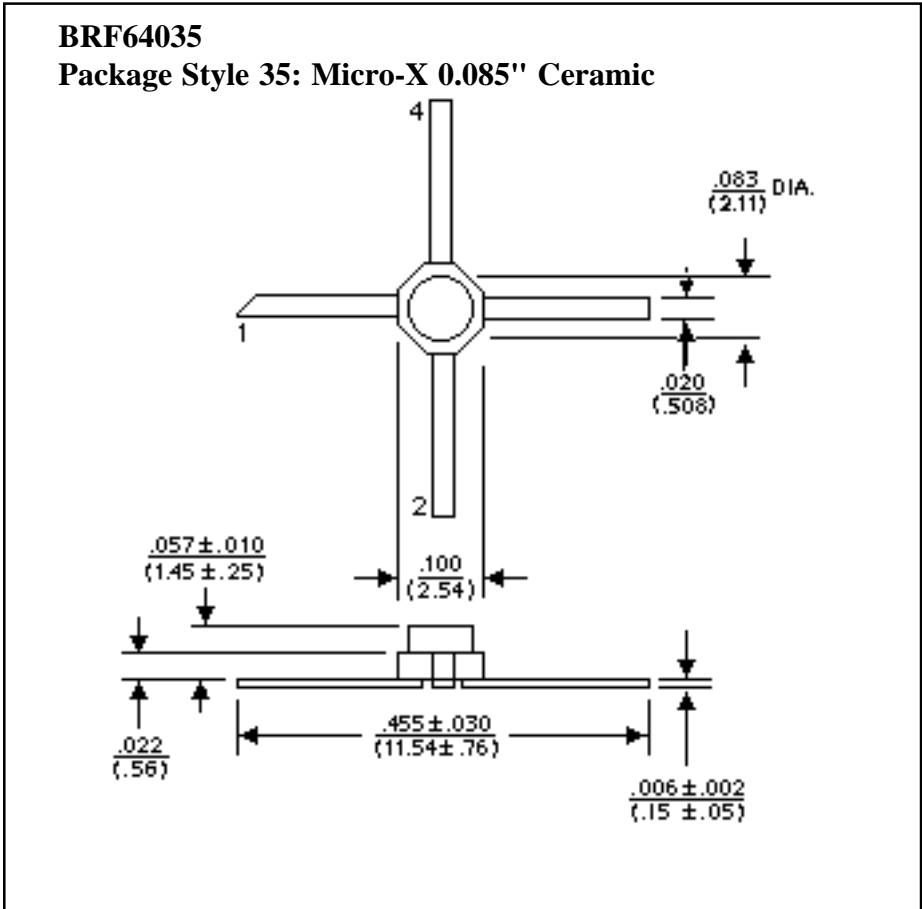
Package Style 92: TO-92



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Part Number BRF640

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| LEAD | 1 | 2 | 3 | 4 |
|----------------------------------|----------|----------|-----------|----------|
| Package Style 14, 85, 35 & 10 | Base | Emitter | Collector | Emitter |

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 Fremont, CA 95131
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NOTES: (unless otherwise specified)

1. Dimensions are $\frac{\text{in}}{\text{mm}}$
2. Tolerances:
 in .xxx = ± .005
 mm .xx = ± .13
3. All dimensions nominal; subject to change without notice